

Title (en)
FIELD EFFECT TRANSISTOR

Title (de)
FELDEFFEKTTRANSISTOR

Title (fr)
TRANSISTOR A EFFET DE CHAMP

Publication
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Application
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Abstract (en)
[origin: WO2006122851A1] The invention relates to a field effect transistor which comprises a source electrode, a drain electrode and a gate electrode. Said field effect transistor comprises a connection between the gate electrode and the source electrode or between the gate electrode and the drain electrode or between the gate electrode and the substrate which carries a leakage current.

IPC 8 full level
H01L 29/51 (2006.01); **H01L 27/06** (2006.01); **H01L 29/06** (2006.01); **H01L 29/78** (2006.01)

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